

**Silicon NPN Power Transistors**

**2SD1291**

**DESCRIPTION**

- With TO-3PN package
- Built-in damper diode
- High voltage ,high reliability
- Wide area of safe operation

**APPLICATIONS**

- For color TV horizontal deflection output applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

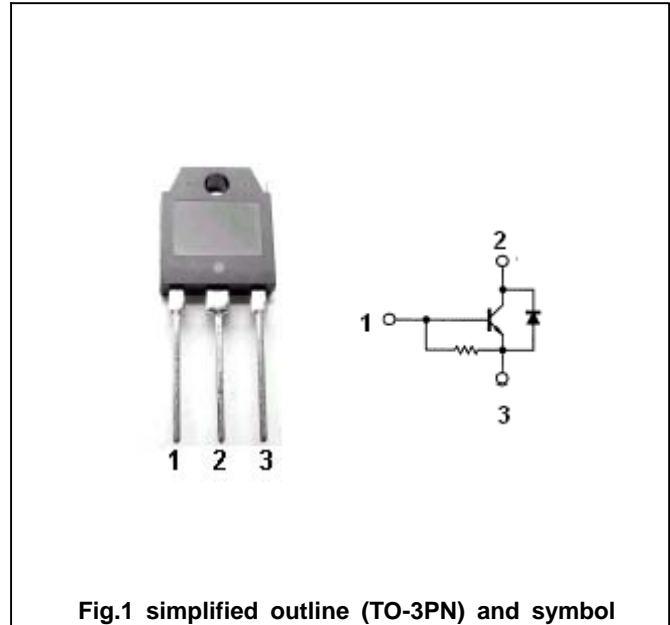


Fig.1 simplified outline (TO-3PN) and symbol

**Absolute maximum ratings (Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current (DC)		3	A
I <sub>CM</sub>	Collector current (Pulse)		13	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	65	W
T <sub>j</sub>	Junction temperature		130	
T <sub>stg</sub>	Storage temperature		-55~130	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =500mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.8A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.8A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =750V; I <sub>E</sub> =0			50	μA
		V <sub>CB</sub> =1500V; I <sub>E</sub> =0			1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2.5A ; V <sub>CE</sub> =10V	4		12	
t <sub>s</sub>	Storage time	I <sub>C</sub> =2.5A I <sub>Leak</sub> =0.8A, L <sub>B</sub> =5 μH	4		8	μs
t <sub>f</sub>	Fall time				1	μs
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> =-4A, I <sub>B</sub> =0			2.2	V

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PACKAGE OUTLINE

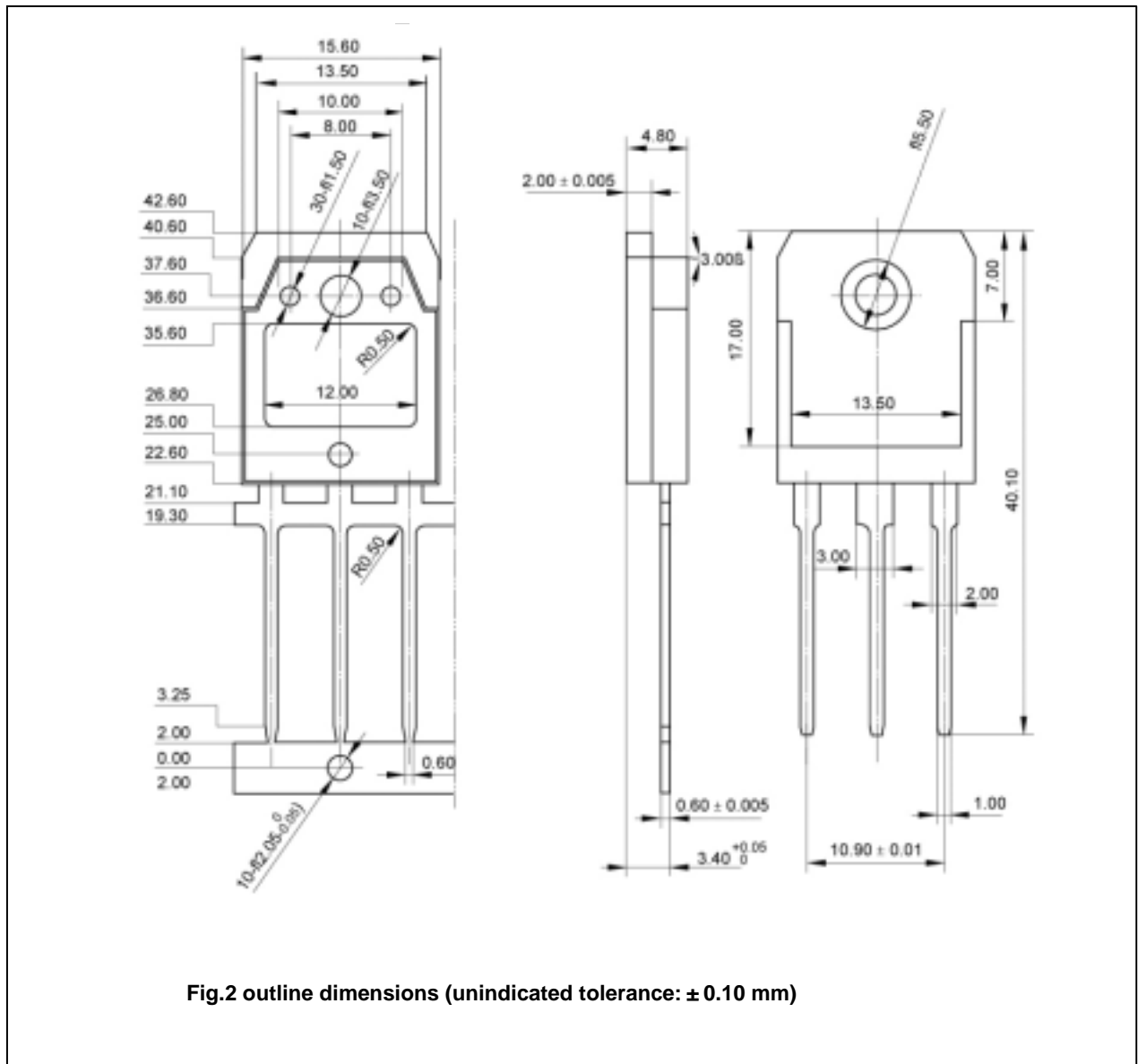


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)